L Number	Hits	Search Text	DB	Time stamp
11	79004		USPAT;	2004/04/19 15:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	263967	oxidize or oxidizing	USPAT;	2004/04/19 15:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
13	9070	ozone same (oxidize or oxidizing)	USPAT;	2004/04/19 15:06
13	30,0	obolic ballic (ontailed of ontaileding)	US-PGPUB;	2001,01,25 25.00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	960	ozone near (oxidize or oxidizing)	USPAT;	2004/04/19 15:07
			US-PGPUB;	
			EPO; JPO;	
	•		DERWENT;	
1.5	1200220		IBM_TDB	2004/04/10 15 05
15	1380328	semiconductor	USPAT;	2004/04/19 15:07
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
16	35	(ozone near (oxidize or oxidizing)) same	USPAT;	2004/04/19 15:08
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	*
			IBM_TDB	
-	6009	1 , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/04/13 09:12
		(438/311) or (438/471) or (438/482) or	US-PGPUB;	
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
_	1	(438/778)).CCLS. (((438/143) or (438/149) or (438/310) or	IBM_TDB	2002/06/05 10:40
-	1	(438/311) or (438/471) or (438/482) or	USPAT; US-PGPUB;	2002/06/05 18:40
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
		(438/778)).CCLS.) and metallic and ((second	IBM_TDB	
		and first) adj (semiconductor (film\$1 or		
		layer\$1))) and amorphous and crystall\$4 and		
		(barrier adj (layer or film)) and (inert adj		
		gas\$2)	1	
-	0	(((438/143) or (438/149) or (438/310) or	USPAT;	2002/06/05 18:16
		(438/311) or (438/471) or (438/482) or	US-PGPUB;	
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or (438/778)).CCLS.) with metallic and ((second	DERWENT;	
		and first) adj (semiconductor (film\$1 or	IBM_TDB	
[		layer\$1))) and amorphous and crystall\$4 and		
		(barrier adj (layer or film)) and (inert adj		
		gas\$2)		
-	1		USPAT;	2002/06/05 18:18
		(438/311) or (438/471) or (438/482) or	US-PGPUB;	
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
		(438/778)).CCLS.) and (metallic or(metal\$4	IBM_TDB	
		adj clusters)) and ((second and first) adj		
		(semiconductor (film\$1 or layer\$1))) and		
		amorphous and crystall\$4 and (barrier adj		
L l		(layer or film)) and (inert adj gas\$2)		

-	1	(((438/143)  or  (438/149)  or  (438/310)  or	USPAT;	2002/06/05 18:20
		(438/311) or (438/471) or (438/482) or	US-PGPUB;	
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (metallic or(metal\$4	DERWENT;	
		adj (cluster\$1 or element\$1))) and ((second	IBM_TDB	
		and first) adj (semiconductor (film\$1 or		
		layer\$1))) and amorphous and crystall\$4 and		1
		(barrier adj (layer or film)) and (inert adj		
1		gas\$2)		
_	1	(((438/143) or (438/149) or (438/310) or	USPAT;	2002/06/05 18:22
	_	(438/311) or (438/471) or (438/482) or	US-PGPUB;	,,
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
i		(438/778)).CCLS.) and (metallic or(metal\$4	IBM TDB	
		adj (cluster\$1 or element\$1))) and ((second	_	
		and first) adj (semiconductor (film\$1 or		
		layer\$1))) and amorphous and crystall\$4 and		
		(barrier adj (layer or film)) and (inert adj		
		gas\$2)and getter\$3		
-	3	(metallic or(metal\$4 adj (cluster\$1 or	USPAT;	2002/06/05 18:25
		element(1))) and ((second and first) adj	US-PGPUB;	
		(semiconductor (film\$1 or layer\$1))) and	EPO; JPO;	
	1	amorphous and crystall\$4 and (barrier adj	DERWENT;	
		(layer or film)) and (inert adj gas\$2)and	IBM_TDB	
	647766	getter\$3	HODAG	2002/11/22 11 ==
-	647766	(metallic or(metal\$4 adj (cluster\$1 or	USPAT;	2003/11/20 14:58
		element\$1)))	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	۰ ا	(metallic or(metal\$4 adj (cluster\$1 or	USPAT;	2002/06/05 18:48
		element\$1))) and ((second and first and	US-PGPUB;	2002/00/03 18:48
		third) adj (semiconductor (film\$1 or	EPO; JPO;	
ĺ		layer\$1))) and amorphous and crystall\$4 and	DERWENT;	
		(barrier adj (layer or film)) and (inert adj	IBM TDB	
		gas\$2)and getter\$3	_	
-	0	(metallic or(metal\$4 adj (cluster\$1 or	USPAT;	2002/06/05 18:30
1	İ	element\$1))) and ((second and first and	US-PGPUB;	
		third) adj (semiconductor (film\$1 or	EPO; JPO;	
		layer\$1))) and amorphous and crystall\$4 and	DERWENT;	
		(barrier adj (layer or film)) and (inert adj	IBM_TDB	
1		gas\$2 adj element) and getter\$3		
-	23348	((second and first and third) adj	USPAT;	2002/06/05 18:34
		(semiconductor (film\$1 or layer\$1)))	US-PGPUB;	
[			EPO; JPO;	
			DERWENT; IBM TDB	
[_	o	(((metallic or(metal\$4 adj (cluster\$1 or	USPAT;	2002/06/05 18:37
		element(1)))) and ( ((second and first and	US-PGPUB;	2002/00/03 18:37
		third) adj (semiconductor (film\$1 or	EPO; JPO;	
		layer\$1))) )) and amorphous and crystall\$4	DERWENT;	
		and (barrier adj (layer or film)) and (inert	IBM TDB	
		adj gas\$2)and getter\$3	_===	
-	3		USPAT;	2002/06/05 18:39
		element\$1))) and ((second and first) adj	US-PGPUB;	
ļ		(film\$1 or layer\$1)) and amorphous and	EPO; JPO;	
		crystall\$4 and (barrier adj (layer or film))	DERWENT;	
		and (inert adj gas\$2)and getter\$3	IBM_TDB	
-	1	((((438/143) or (438/149) or (438/310) or	USPAT;	2002/06/05 18:41
		(438/311) or (438/471) or (438/482) or	US-PGPUB;	
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
		(438/778)).CCLS.) and metallic and ((second	IBM_TDB	
		and first) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4 and		
[		(barrier adj (layer or film)) and (inert adj		
		gas\$2)) and getter\$3	İ	
LL		gabys, and getterys		

-	15096	getter\$3	USPAT; US-PGPUB;	2002/06/05 20:26
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2810	,,	USPAT;	2002/06/05 18:43
		element\$1)))) and getter\$3	US-PGPUB; EPO; JPO;	
			DERWENT;	
	12	/ //motollin or/matol64 add /alvatov61 av	IBM_TDB	0000/05/05 10 11
-	12	( ((metallic or(metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3) and amorphous	USPAT; US-PGPUB;	2002/06/05 18:44
		and crystall\$4 and (barrier adj (layer or	EPO; JPO;	
1		film)) and (inert adj gas\$2)	DERWENT;	
-	0	(metallic or(metal\$4 or (metal\$4 adj	IBM_TDB USPAT;	2002/06/05 18:52
	}	(cluster\$1 or element\$1)))) and ((second and	US-PGPUB;	
		first and third) adj (semiconductor (film\$1 or layer\$1))) and amorphous and crystall\$4	EPO; JPO; DERWENT;	
		and (barrier adj (layer or film)) and (inert	IBM TDB	
	0	adj gas\$2)and getter\$3		
_	0	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and ((first and	USPAT; US-PGPUB;	2002/06/05 18:54
		second and third) adj (film\$1 or layer\$1))	EPO; JPO;	
		and amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj	DERWENT;	
		gas\$2)and getter\$3	IBM_TDB	
-	5	(metallic or(metal\$4 or (metal\$4 adj	USPAT;	2002/06/05 20:27
		(cluster\$1 or element\$1)))) and (first adj (film\$1 or layer\$1)) and amorphous and	US-PGPUB; EPO; JPO;	
		crystall\$4 and (barrier adj (layer or film))	DERWENT;	
	9	and (inert adj gas\$2) and getter\$3	IBM_TDB	
-	9	(metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and	USPAT; US-PGPUB;	2002/06/05 18:56
		(semiconductor adj (film\$1 or layer\$1)) and	EPO; JPO;	
		amorphous and crystall\$4 and (barrier adj (layer or film)) and (inert adj gas\$2)and	DERWENT;	
		getter\$3	IBM_TDB	
_	8595	· · · · · · · · · · · · · · · · · · ·	USPAT;	2002/06/05 20:28
		(cluster\$1 or element\$1)))) and getter\$3	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	0	(metallic or(metal\$4 or (metal\$4 adj	IBM_TDB USPAT;	2002/06/05 20:31
		(cluster\$1 or element\$1)))) and getter\$3 and	US-PGPUB;	2002/06/03 20:31
		amorphrous	EPO; JPO;	
			DERWENT; IBM TDB	
-	1086	(metallic or(metal\$4 or (metal\$4 adj	USPAT;	2002/06/05 20:32
		(cluster\$1 or element\$1)))) and getter\$3 and amorphous	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	715	(/metallic or/metal\$4 or /matal\$4 add	IBM_TDB	2002/05/25 22 35
	113	((metallic or(metal\$4 or (metal\$4 adj (cluster\$1 or element\$1)))) and getter\$3 and	USPAT; US-PGPUB;	2002/06/05 20:32
		amorphous) and crystall\$4	EPO; JPO;	
			DERWENT;	
<b>-</b>	189	(((metallic or(metal\$4 or (metal\$4 adj	IBM_TDB USPAT;	2002/06/05 20:33
		(cluster\$1 or element\$1)))) and getter\$3 and	US-PGPUB;	. ,
		amorphous) and crystall\$4) and inert adj gas\$2	EPO; JPO; DERWENT;	
			IBM_TDB	
-	14	<pre>((((metallic or(metal\$4 or (metal\$4 adj   (cluster\$1 or element\$1)))) and getter\$3 and</pre>	USPAT; US-PGPUB;	2002/06/05 20:33
		amorphous) and crystall\$4) and inert adj	EPO; JPO;	
		gas\$2) and (barrier adj (layer or film))	DERWENT;	
-	6	(("6087679") or ("6077731") or ("6147667")	<pre>IBM_TDB USPAT;</pre>	2002/06/07 13:54
		or ("6133073") or ("6168980") or	US-PGPUB	111, 10, 0, 10, 51
L		("6107639")).PN.		

-	4	((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or	USPAT; US-PGPUB	2002/06/07 14:52
-	3	("6107639")).PN.) and barrier (((("6087679") or ("6077731") or ("6147667") or ("6133073") or ("6168980") or	USPAT; US-PGPUB	2002/06/07 14:51
_	1	("6107639")).PN.) and barrier) and block\$3 (("6396147").PN.) and barrier	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((("6396147").PN.) and barrier) and	USPAT; US-PGPUB	2002/06/07 14:53
-	1	amorphous (((("6396147").PN.) and barrier) and amorphous) and crystal\$4	USPAT; US-PGPUB	2002/06/07 14:53
-	1	((((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas	USPAT; US-PGPUB	2002/06/07 14:54
-	1	((((("6396147").PN.) and barrier) and amorphous) and crystal\$4) and inert adj gas)	USPAT; US-PGPUB	2002/06/07 14:54
		and getter\$3	00 10105	
-	835	1	USPAT; US-PGPUB	2002/06/08 13:58
-	215	(((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3	USPAT; US-PGPUB	2002/06/08 14:43
-	28	((((438/166) or (438/486) or	USPAT;	2002/06/08 14:43
		(438/476)).CCLS.) and getter\$3) and (inert or noble) adj gas	US-PGPUB	
-	9	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and (inert	USPAT; US-PGPUB	2002/06/08 14:44
		or noble) adj gas) and barrier	apam	2000/05/00 11 00
-	0	("FOR0146").PN.	USPAT; US-PGPUB	2002/06/08 14:08
-	0	("FOR0146").PN.	JPO; DERWENT;	2002/06/10 19:02
			IBM TDB	
-	96	(438/476)).CCLS.) and getter\$3) and	USPAT; US-PGPUB	2002/06/08 14:43
	1.0	amorphous	HCDAM.	2002/06/00 14 42
-	10	(((((438/166) or (438/486) or (438/476)).CCLS.) and getter\$3) and	USPAT; US-PGPUB	2002/06/08 14:43
-	6	· · · · · · · · · · · · · · · · · · ·	USPAT;	2002/06/08 14:44
		(438/476)).CCLS.) and getter\$3) and amorphous) and (inert or noble) adj gas) and barrier	US-PGPUB	
-	1	("6396147").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	1	("5789284").PN.	USPAT; US-PGPUB	2002/06/10 17:37
-	0	("FOR 146").PN.	JPO;	2002/06/10 19:04
			DERWENT; IBM_TDB	
-	9	<pre>(metallic or(metal\$4 adj (cluster\$1 or element\$1))) with (anneal\$ with (electric</pre>	USPAT; US-PGPUB;	2002/06/21 16:53
		adj current))	EPO; JPO; DERWENT;	
	-	(#20020086469#\ PM	IBM_TDB	2002/06/02 17 02
-	1	("20020086469").PN.	USPAT; US-PGPUB	2003/06/02 17:02
_	19346	kim.in.	USPAT; US-PGPUB	2003/06/02 17:02
-	8679	getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	44	kim.in. and getter\$3	USPAT; US-PGPUB	2003/06/02 17:03
-	16337	getter\$3 or getter	USPAT; US-PGPUB;	2003/06/03 13:50
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2089	"semiconductor energy laboratory"	USPAT; US-PGPUB	2003/06/03 13:52
-	19706	tft or (thin adj film adj transistor)	USPAT; US-PGPUB	2003/06/03 13:58

_	641	(getter\$3 or getter) and (tft or (thin adj	USPAT:	2003/06/03 14:00
	041	film adj transistor))	US-PGPUB	
-	248	((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor	USPAT; US-PGPUB	2003/06/03 14:00
-	40	energy laboratory" ((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not	USPAT; US-PGPUB	2003/06/03 14:02
	141	"semiconductor energy laboratory") and @ad<20010216) and 438/\$.ccls.	HODAE	2002/05/02 10 02
-	111	<pre>(((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad&lt;20010216</pre>	USPAT; US-PGPUB	2003/06/03 18:03
-	32627	ozone	USPAT; US-PGPUB	2003/06/03 18:02
-	110	(((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216	USPAT; US-PGPUB	2003/06/03 18:03
-	3		USPAT; US-PGPUB	2003/06/03 18:12
-	66319		USPAT; US-PGPUB	2003/06/03 18:13
-	0	((((getter\$3 or getter) and (tft or (thin adj film adj transistor))) not "semiconductor energy laboratory") and @ad<20010216) and deioniz\$3	USPAT; US-PGPUB	2003/06/03 18:13
-	556		USPAT; US-PGPUB	2003/06/06 12:37
-	18319	amorphous\$3 and crystal\$8 and laser	USPAT; US-PGPUB	2003/06/06 12:38
-	692277		USPAT; US-PGPUB	2003/06/06 12:38
-	61	(((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)	USPAT; US-PGPUB	2003/06/06 12:38
-	57	((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))	USPAT; US-PGPUB	2003/06/06 14:19
-	57		USPAT; US-PGPUB	2003/06/06 14:22
-	5183	catalytic near metal	USPAT; US-PGPUB	2003/06/06 14:24
-	1	(((((483/471) or (438/472) or (438/473) or (438/474) or (438/475) or (438/476) or (438/477)).CCLS.) and (amorphous\$3 and crystal\$8 and laser)) and (barrier or (oxide or nitride or oxynitride))) and (catalytic	USPAT; US-PGPUB	2003/06/06 14:21
_	112610	near metal) amorphous\$3	USPAT;	2003/06/06 14:22
-	505011	crystal\$8	US-PGPUB USPAT;	2003/06/06 14:23
-	260315	laser	US-PGPUB USPAT; US-PGPUB	2003/06/06 14:23
-	692277	barrier or (oxide or nitride or oxynitride)	USPAT; US-PGPUB	2004/04/13 09:13
-	28707	(catalytic or cluster or element) near metal	USPAT; US-PGPUB	2003/06/06 14:25
-	2556	<pre>crystal\$8 same ((catalytic or cluster or element) near metal )</pre>	USPAT; US-PGPUB	2003/06/06 14:25
-	1285	<pre>( crystal\$8 same ((catalytic or cluster or element) near metal )) and amorphous\$3</pre>	USPAT; US-PGPUB	2003/06/06 14:25

-	709	((crystal\$8 same ((catalytic or cluster or element) near metal )) and amorphous\$3 ) and laser	USPAT; US-PGPUB	2003/06/06 14:26
-	676		USPAT; US-PGPUB	2003/06/06 14:26
-	8423	oxynitride)) getter or gettering	USPAT;	2003/06/06 14:26
-	233	(((( crystal\$8 same ((catalytic or cluster or element) near metal )) and amorphous\$3 ) and laser) and (barrier or (oxide or	US-PGPUB USPAT; US-PGPUB	2003/06/06 14:45
	5626607	nitride or oxynitride))) and (getter or gettering)	IIODAM.	2003/06/06 14 50
-	5636607	(fe or iron) or (co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or	USPAT; US-PGPUB	2003/06/06 14:50
-	124463	iridium) or (pt or platinum) or (au or gold) ((fe or iron) or( co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or	USPAT; US-PGPUB	2003/06/06 14:51
-	29298	cobalt) or (ni or nickel) or (cu or copper)	USPAT; US-PGPUB	2003/06/06 14:51
		or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)		
-	22525		USPAT; US-PGPUB	2003/06/06 14:51
		or iridium) or (pt or platinum) or (au or gold)) same crystal\$8) ) and (barrier or (oxide or nitride or oxynitride))		
-	690	((amorphous\$3 and (((fe or iron) or (co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8) ) and (barrier or (oxide or nitride or oxynitride))) and (getter or gettering)	USPAT; US-PGPUB	2003/06/06 14:52
-	531		USPAT; US-PGPUB	2003/06/06 14:52
-	133656	(barrier or (oxide or nitride or oxynitride)) near (film or layer)	USPAT; US-PGPUB	2003/06/06 15:23
-	14785	((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or (co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or	USPAT; US-PGPUB	2003/06/06 15:23
-	6367	<pre>(rh or rhodium) or (pd or palladium) or (os or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8) (((barrier or (oxide or nitride or oxynitride)) near (film or layer)) and (((fe or iron) or( co or cobalt) or (ni or nickel) or (cu or copper) or (ru or ruthenium) or (rh or rhodium) or (pd or palladium) or (os</pre>	USPAT; US-PGPUB	2003/06/06 15:24
		or osmium) or (ir or iridium) or (pt or platinum) or (au or gold)) same crystal\$8)) and amorphous\$3		

-	614	((((barrier or (oxide or nitride or	USPAT;	2003/06/06 15:24
		oxynitride)) near (film or layer)) and (((fe	US-PGPUB	
		or iron) or (co or cobalt) or (ni or nickel)		
		or (cu or copper) or (ru or ruthenium) or		
		(rh or rhodium) or (pd or palladium) or (os		
		or osmium) or (ir or iridium) or (pt or		
1		platinum) or (au or gold)) same crystal\$8))		
		and amorphous\$3 ) and (getter or gettering)		
-	511	1	USPAT;	2003/06/06 15:24
	İ	oxynitride)) near (film or layer)) and (((fe	US-PGPUB	į.
		or iron) or (co or cobalt) or (ni or nickel)		
		or (cu or copper) or (ru or ruthenium) or		
		(rh or rhodium) or (pd or palladium) or (os		
		or osmium) or (ir or iridium) or (pt or		
		platinum) or (au or gold)) same crystal\$8))		
	1			
		and amorphous\$3 ) and (getter or gettering))		
		and laser ·		
-	44	5821138.URPN.	USPAT	2003/06/06 15:49
-	5	("4838654"   "5376561"   "5488012"	USPAT	2003/06/06 15:54
	İ	"5529937"   "5618739").PN.		
-	13	("4024626"   "4759610"   "4771016"	USPAT	2003/06/06 15:54
1	1	"4838654"   "4885616"   "4906587"	]	
	1	"4968638"   "4980308"   "4984033"		
		"5110748"   "5206749"   "5256562"		1
		1		
		"5455187").PN.		
-	13	("4024626"   "4759610"   "4771016"	USPAT	2003/06/06 15:54
		"4838654"   "4885616"   "4906587"		
	}	"4968638"   "4980308"   "4984033"		
		"5110748"   "5206749"   "5256562"		1
	]	"5455187").PN.		
l <u>-</u>	0	6337259.URPN.	USPAT	2003/06/06 16:14
_	ı	"6140166".PN.		2003/06/06 16:14
-			USPAT	1
-	0	6337259.URPN.	USPAT	2003/06/06 16:15
-	0	6376336.URPN.	USPAT	2003/06/06 17:06
-	30	("3936858"   "4498227"   "5194395"	USPAT	2003/06/06 17:06
		"5244819"   "5272104"   "5443661"		
		"5453153"   "5501993"   "5646053"		
		"5753560"   "5773152"   "5795809"		
		"5807771"   "5818085"   "5882990"		
		"5899732"	1	
	ŀ	"5965917"   "5976956"   "6001711"		
		"6010950"   "6013584"   "6022793"		<u> </u>
		"6024888"   "6083324"   "6093624"		
	1	"6100202"   "6114223"   "6133123").PN.		
] -	1	("5605847").PN.	USPAT;	2003/06/15 11:57
			US-PGPUB	
-	1	("6097037").PN.	USPAT;	2003/06/15 11:57
	1		US-PGPUB	-000,00,10 11.0,
l <u>-</u>	1	("6337259").PN.		2002/06/15 12:10
-		( 0331239 ) .FN.	USPAT;	2003/06/15 12:10
			US-PGPUB	
-	36	funai.in.	USPAT;	2003/06/15 16:13
			US-PGPUB	
-	1	("5550070").PN.	USPAT;	2003/06/15 16:49
			US-PGPUB	
_	7255	((438/143) or (438/149) or (438/310) or	USPAT;	2003/11/20 14:20
	, 233	(438/311) or (438/471) or (438/482) or		2003/11/20 14:20
			US-PGPUB;	1
		(438/488) or (438/761) or (438/762) or	EPO; JPO;	
		(438/763) or (438/764) or (438/765) or	DERWENT;	
		(438/778)).CCLS.	IBM_TDB	
-	9600	noble near gas	USPAT;	2003/11/20 14:17
		_	US-PGPUB;	
			EPO; JPO;	l i
	1			
			DERWENT;	
	200000	amaal an haak maana ku i	IBM_TDB	
_	260833	anneal or heat near2 treatment	USPAT;	2003/11/20 14:18
	1		US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
			IBM TDB	

-	12617	getter	USPAT; US-PGPUB; EPO; JPO;	2003/11/20 14:50
			DERWENT; IBM TDB	
-	205	(438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or	USPAT; US-PGPUB; EPO; JPO;	2003/11/20 14:20
-	5	(438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter ((((438/143) or (438/149) or (438/310) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or (438/311) or	DERWENT; IBM_TDB USPAT;	2003/11/20 14:19
		(438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and getter) and (noble near gas)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
-	1598	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (anneal or heat near2 treatment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:21
-	66	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (noble near gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/20 14:33
-	56		IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/20 14:44
-	230662	helium or neon or argon or krypton or xenon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/21 12:05
-	1114	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
-	424	l = -	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
-	30	(((((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (helium or neon or argon or krypton or xenon)) and (anneal or heat near2 treatment)) and getter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/20 14:46
	16843	getter or gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/20 14:50
-	3575	(helium or neon or argon or krypton or xenon) and (getter or gettering)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/20 14:51
-	1152	((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/20 14:51

_	711655	<pre>(metallic or(metal\$4 adj (cluster\$1 or element\$1)))</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/11/20 14:58
			DERWENT; IBM TDB	
-	579	(((helium or neon or argon or krypton or xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and	USPAT; US-PGPUB; EPO; JPO;	2003/11/20 14:59
		((metallic or(metal\$4 adj (cluster\$1 or element\$1))))	DERWENT; IBM_TDB	
-	1303417	semiconductor	USPAT; US-PGPUB; EPO; JPO;	2003/11/20 14:59
_	464		DERWENT; IBM_TDB USPAT;	2003/11/20 15:00
		<pre>xenon) and (getter or gettering)) and (anneal or heat near2 treatment)) and ((metallic or(metal\$4 adj (cluster\$1 or element\$1))))) and semiconductor</pre>	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
-	210593	amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/20 15:00
-	305	(((((helium or neon or argon or krypton or xenon) and (getter or gettering)) and	IBM_TDB USPAT; US-PGPUB;	2003/11/20 15:36
:		<pre>(anneal or heat near2 treatment)) and   ((metallic or(metal\$4 adj (cluster\$1 or   element\$1))))) and semiconductor) and   amorphous</pre>	EPO; JPO; DERWENT; IBM_TDB	
-	5	("5696003").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/20 15:36
-	35 17	5696003.URPN. ("3783049"   "4068020"   "4309223"	IBM_TDB USPAT USPAT	2003/11/20 15:37 2003/11/20 15:58
		"5147826"   "5275851"   "5278093"   "5289030"   "5403772"   "5481121"   "5488000"   "5501989"   "5508533"   "5529937"   "5531182"   "5534716"   "5543352"   "5569610").PN.		
-	37	"5696003"	USPAT; US-PGPUB	2003/11/20 16:22
-	1	(("5696003").PN.) and (helium or neon or argon or krypton or xenon)	USPAT; US-PGPUB	2003/11/20 16:23
_	1990466	("5505070").PN.  (He or helium) or (Ne or neon) or (Ar or	USPAT; US-PGPUB USPAT;	2003/11/20 16:48 2003/11/21 12:13
	1990400	argon) or (Kr or krypton) or (Xe or xenon)	US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:13
-	51494	crystallize or crystalling	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/21 12:14
-	82959	polycrystalline	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/11/21 12:15
			EPO; JPO; DERWENT; IBM_TDB	
-	15068	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystalling)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:29
			IBM_TDB	

-	1413	(((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) and (crystallize or crystalling)) and	USPAT; US-PGPUB; EPO; JPO;	2003/11/21 12:15
		polycrystalline	DERWENT; IBM_TDB	
-	14	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near (crystallize or crystalling)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:29
-	139342	implant or implanting	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/21 12:35
-	230817	(implant or implanting) or (dope or doping)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:36
-	467	((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:36
-	2	(((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) same (crystallize or crystalling)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:38
_	15	(((He or helium) or (Ne or neon) or (Ar or argon) or (Kr or krypton) or (Xe or xenon)) near ((implant or implanting) or (dope or doping))) and (crystallize or crystalling)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/21 12:38
-	1	("6391690").PN.	IBM_TDB USPAT; US-PGPUB	2003/11/21 13:08
-	5986	getter	USPAT; US-PGPUB	2003/11/21 13:08
-	0	(("6391690").PN.) and getter	USPAT; US-PGPUB	2003/11/21 13:08
-	1	"6337259"	USPAT; US-PGPUB	2003/11/21 13:19
-	1	laser and "6337259"	USPAT; US-PGPUB	2003/11/21 13:19
_	1	("5696003").PN.	USPAT; US-PGPUB	2003/11/21 13:41
-	7538	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:12
-	783211	(438/778)).CCLS. barrier or (oxide or nitride or oxynitride)	IBM_TDB USPAT;	2004/04/13 09:15
-	400286	(barrier or (oxide or nitride or oxynitride)) near2 (film or layer)	US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:16
-	147288	semiconductor near (film or layer)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:16
_	17881	getter or gettering	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:16
L			IBM_TDB	

-	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:16
-	907	(((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/13 09:16
-	122	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and ((((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:20
-	29458	((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:20
-	2602	Semiconductor adj energy adj laboratory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:22
-	2542	(Semiconductor adj energy adj laboratory) not ((((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:22
-	62	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (semiconductor near (film or layer))) and (getter or gettering))) not (Semiconductor adj energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/13 09:34
-	0	second near semiconuctor near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:38
-	8543	second near semiconductor near2 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:38
-	1239	<pre>((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:39
-	80	<pre>(((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:39
-	43	<pre>((((barrier or (oxide or nitride or oxynitride)) near2 (film or layer)) same (second near semiconductor near2 (film or layer))) and (getter or gettering)) not (Semiconductor adj energy adj laboratory)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/13 09:39

-	4	(((((barrier or (oxide or nitride or	USPAT;	2004/04/13 09:40
		oxynitride)) near2 (film or layer)) same	US-PGPUB;	
		(second near semiconductor near2 (film or	EPO; JPO;	
		layer))) and (getter or gettering)) not	DERWENT;	
		(Semiconductor adj energy adj laboratory))	IBM_TDB	
		and (((438/143) or (438/149) or (438/310) or		
		(438/311) or (438/471) or (438/482) or	i	
		(438/488) or (438/761) or (438/762) or		
		(438/763) or (438/764) or (438/765) or		
		(438/778)).CCLS.)		
-	4	Semiconductor adj energy adj laboratories	USPAT;	2004/04/18 18:47
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0.500		IBM_TDB	
-	2600	Semiconductor adj energy adj laboratory	USPAT;	2004/04/18 18:51
			US-PGPUB;	
	1		EPO; JPO;	
[	1		DERWENT;	
1_	17891	getter or gettering	IBM_TDB	2004/04/10 10 55
-	1/891	decret of decretting	USPAT;	2004/04/18 18:51
			US-PGPUB;	
	1		EPO; JPO; DERWENT;	
1	1		IBM TDB	
_	571	(Semiconductor adj energy adj laboratory)	USPAT;	2004/04/18 18:51
	1	and (getter or gettering)	US-PGPUB;	2004/04/18 18.31
		data (geodel of geodeling)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	191804	inert adj qas	USPAT;	2004/04/18 18:52
			US-PGPUB;	,,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	205	((Semiconductor adj energy adj laboratory)	USPAT;	2004/04/18 18:52
		and (getter or gettering)) and (inert adj	US-PGPUB;	
		gas)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
<del>-</del>	204382	semiconductor near2 (film or layer)	USPAT;	2004/04/18 18:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u>-</u>	205	(((Semiconductor adj energy adj laboratory)	IBM_TDB	2004/04/10 10 05
-	205	and (getter or gettering)) and (inert adj	USPAT; US-PGPUB;	2004/04/18 19:05
		gas)) and (semiconductor near2 (film or	EPO; JPO;	
		layer))	DERWENT;	
		14,02,,	IBM TDB	
_	97068	barrier near2 (layer or film)	USPAT;	2004/04/18 19:06
	1 2,000	Tarita indica (Idjoi of IIIm)	US-PGPUB:	2007/04/10 17:00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	55	((((Semiconductor adj energy adj laboratory)	USPAT;	2004/04/18 19:26
		and (getter or gettering)) and (inert adj	US-PGPUB;	
		gas)) and (semiconductor near2 (film or	EPO; JPO;	
ĺ		layer))) and (barrier near2 (layer or film))	DERWENT;	
		l	IBM_TDB	
	2	(("6048758") or ("5248630")).PN.	USPAT	2004/04/19 15:05